

## SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

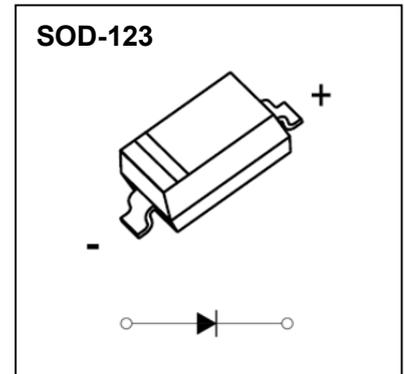
### Features

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

### Applications

- High speed switching

Marking:S8



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	40	V
Reverse Voltage	$V_R$	30	V
Mean Rectifying Current	$I_O$	30	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	$I_{FSM}$	200	mA
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 40 to + 125	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$	$V_F$	-	0.37	V
Reverse Current at $V_R = 30\text{ V}$	$I_R$	-	0.5	$\mu\text{A}$
Capacitance Between Terminals at $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	2	-	pF

Note: ESD sensitive product handling required.

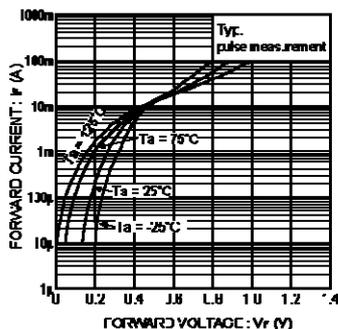


Fig. 1 Forward characteristics

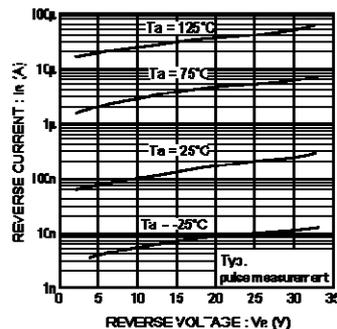


Fig. 2 Reverse characteristics

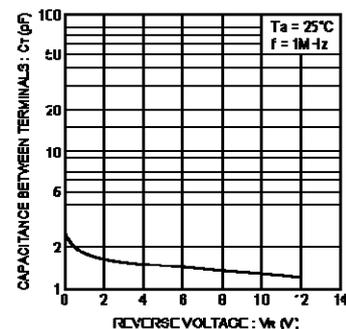


Fig. 3 Capacitance between terminals characteristics